

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Canceled).

Claim 2 (Currently Amended): A magnetoresistance effect element comprising:
a stacked film including a magnetization fixed layer in which the direction of magnetization is substantially fixed to one direction, and a magnetization free layer in which the direction of magnetization varies in accordance with an external magnetic field; and
an electrode connected to a part of a principal plane of the stacked film,
the magnetoresistance effect element having a resistance varying in response to a relative angle between the direction of magnetization in the magnetization fixed layer and the direction of magnetization in the magnetization free layer, ~~[[said]]~~ the resistance being detected when a sense current is applied to the film planes of the magnetization fixed layer and the magnetization free layer via the electrode in a direction substantially perpendicular to the magnetization fixed layer and the magnetization free layer,
~~the magnetoresistance effect element having a single conductive part with a film area smaller than a film area of the magnetoresistance effect element and the magnetoresistance effect element is configured such that the sense current flows only through said single conductive part, and~~
the electrode comprising:
a single pillar electrode portion substantially perpendicularly extending from the principal plane of the stacked film and having a sectional film area smaller than an area of the principal plane of the stacked film, and

a feed portion connected to the single pillar electrode portion and extending from the single pillar electrode portion substantially in parallel to the principal plane of the stacked film, and
the magnetoresistance effect element being configured such that the sense current flows only through the single pillar electrode portion.

Claim 3 (Currently Amended): A magnetoresistance effect element as set forth in claim 2, wherein the sectional area of the feed portion substantially in parallel to the principal plane of the stacked film is greater than the sectional area of the single pillar electrode portion.

Claim 4 (Currently Amended): A magnetoresistance effect element as set forth in claim 2, wherein the shape of a contact surface of the principal plane of the stacked film contacting the single pillar electrode portion is substantially a quadrilateral.

Claim 5 (Currently Amended): A magnetoresistance effect element comprising:
a stacked film including a magnetization fixed layer in which the direction of magnetization is substantially fixed to one direction, and a magnetization free layer in which the direction of magnetization varies in response to an external magnetic field; and
two electrodes, each of which is connected to a part of a corresponding one of both principal planes of the stacked film,
the magnetoresistance effect element having a resistance varying in response to a relative angle between the direction of magnetization in the magnetization fixed layer and the direction of magnetization in the magnetization free layer, the resistance being detected when

a sense current is applied to the film planes of the magnetization fixed layer and the magnetization free layer via the two electrode electrodes in a direction substantially perpendicular to the magnetization fixed layer and the magnetization free layer,

~~the magnetoresistance effect element having a single conductive part with a film area smaller than a film area of the magnetoresistance effect element and the magnetoresistance effect element is configured such that the sense current flows only through said single conductive part, and~~

each of the two electrodes comprising:

a single pillar electrode portion substantially perpendicularly extending from the corresponding one of the both principal planes of the stacked film and having a sectional film area smaller than an area of the corresponding area of both principal planes of the stacked film, and

a feed portion being connected to the single pillar electrode portion and extending from the single pillar electrode portion substantially in parallel to the both principal planes of the stacked film, and

the magnetoresistance effect element being configured such that the sense current flows only through the single pillar electrode portions.

Claim 6 (Currently Amended): A magnetoresistance effect element as set forth in claim 5, wherein the sectional area of the feed portion substantially in parallel to the both principal planes of the stacked film is greater than the sectional area of the single pillar electrode portion.

Claim 7 (Currently Amended): A magnetoresistance effect element as set forth in claim 5, wherein the shape of a contact surface of each of the both principal planes of the stacked film contacting the single pillar electrode portion is substantially a quadrilateral.

Claims 8-16 (Canceled).

Claim 17 (Original): A magnetic head having a magnetoresistance effect element as set forth in claim 2.

Claim 18 (Original): A magnetic head having a magnetoresistance effect element as set forth in claim 5.

Claim 19 (Canceled).

Claim 20 (Original): A magnetic reproducing system which has a magnetic head as set forth in claim 18 and which is capable of reading magnetic information stored in a magnetic recording medium.